INTEGRATED CIRCUITS

DATA SHEET

TEA1065

Versatile telephone transmission circuit with dialler interface

Product specification
File under Integrated Circuits, IC03A

March 1994





Versatile telephone transmission circuit with dialler interface

TEA1065

FEATURES

- Current and voltage regulator mode with adjustable static resistances
- · Provides supply for external circuitry
- Symmetrical high-impedance inputs for piezoelectric microphone
- Asymmetrical high-impedance input for electret microphone
- · DTMF signal input with confidence tone
- · Mute input for pulse or DTMF dialling
- · Power-down input for pulse dial or register recall
- Digital pulse input to drive an external switch transistor
- Receiving amplifier for magnetic, dynamic or piezoelectric earpieces

- Large gain setting range on microphone and earpiece amplifiers
- Line loss compensation facility, line current dependent (on microphone and earpiece amplifiers)
- Adjustable gain control
- · DC line voltage adjustment facility

GENERAL DESCRIPTION

The TEA1065 is a bipolar integrated circuit which performs all speech and line interface functions that are required in fully electronic telephone sets with adjustable DC mask. The circuit performs electronic switching between dialling and speech internally.

ORDERING INFORMATION

EXTENDED TYPE	PACKAGE						
NUMBER	PINS	PIN POSITION	MATERIAL	CODE			
TEA1065	24	DIL	plastic	SOT101L			
TEA1065T	24	SO24	plastic	SOT137A			

Notes

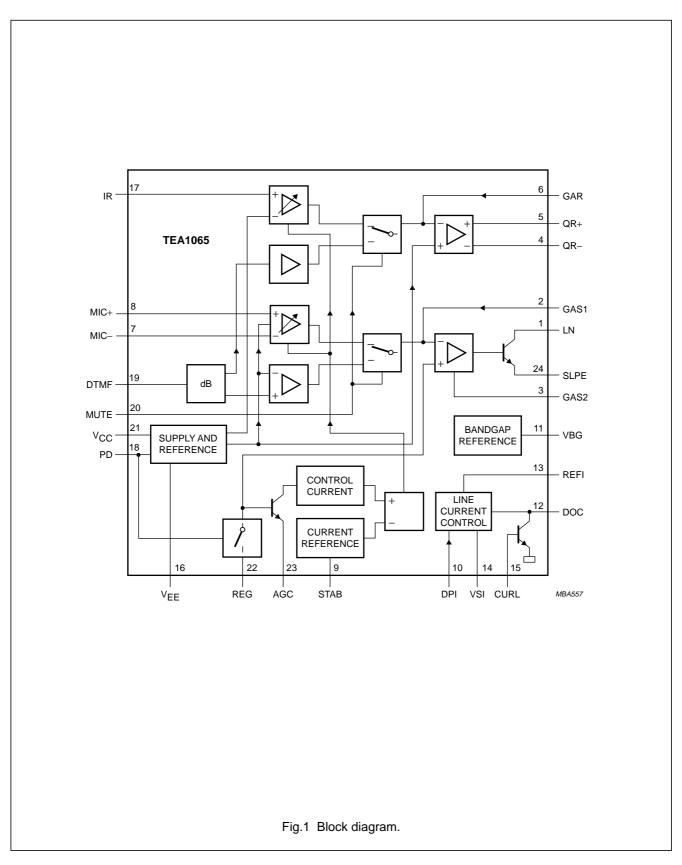
SOT101-1; 1998 Jun 18.
 SOT137-1; 1998 Jun 18.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{LN}	line voltage	I _{line} = 15 mA	4.25	4.45	4.65	V
I _{line}	normal operation line current range		10	_	150	mA
I _{CC}	internal supply consumption					
	power-down input LOW		_	1.14	1.5	mA
	power-down input HIGH		_	73	105	μΑ
V _{CC}	supply voltage for peripherals	I _{line} = 15 mA;				
		MUTE input HIGH				
		I _P = 1.2 mA	2.7	_	_	V
		I _P = 1.55 mA	2.5	_	_	V
G _V	voltage gain range					
	microphone amplifier		30	_	46	dB
	earpiece amplifier		20	_	45	dB
ΔG_V	line loss compensation					
	gain control range		-5.5	-5.9	-6.3	dB
T _{amb}	operating ambient temperature range		-25	_	+75	°C

Versatile telephone transmission circuit with dialler interface

TEA1065

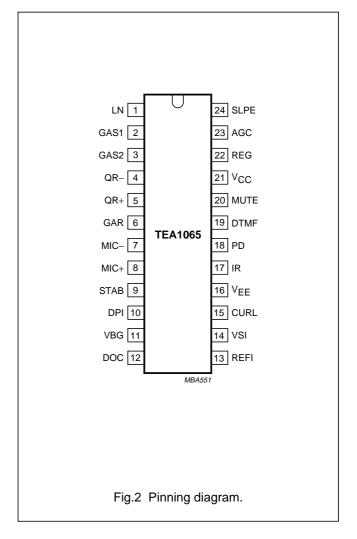


Versatile telephone transmission circuit with dialler interface

TEA1065

PINNING

SYMBOL	PIN	DESCRIPTION
LN	1	positive line terminal
GAS1	2	gain adjustment; sending amplifier
GAS2	3	gain adjustment; sending amplifier
QR-	4	inverting output; receiving amplifier
QR+	5	non-inverting output; receiving amplifier
GAR	6	gain adjustment; receiving amplifier
MIC-	7	inverting microphone input
MIC+	8	non-inverting microphone input
STAB	9	current stabilizer
DPI	10	digital pulse input
VBG	11	bandgap output reference
DOC	12	drive current output
REFI	13	reference voltage input
VSI	14	voltage sense input
CURL	15	current limitation input
V _{EE}	16	negative line terminal
IR	17	receiving amplifier input
PD	18	power-down input
DTMF	19	dual-tone multifrequency input
MUTE	20	MUTE input
V _{CC}	21	positive supply decoupling
REG	22	voltage regulator decoupling
AGC	23	automatic gain control input
SLPE	24	slope (DC resistance) adjustment



Versatile telephone transmission circuit with dialler interface

TEA1065

FUNCTIONAL DESCRIPTION

Supply: V_{CC}, LN, SLPE, REG and STAB

The circuit and its peripherals are usually supplied from the telephone line. The circuit develops its own supply voltage at V_{CC} (pin 21) and regulates its voltage drop between LN and SLPE (pins 1 and 24). The internal supply requires a decoupling capacitor between V_{CC} and V_{EE} (pin 16); the internal voltage regulator has to be decoupled by a capacitor from REG (pin 22) to V_{EE} . The internal current stabilizer is set by a 3.6 k Ω resistor connected between STAB (pin 9) and V_{EE} .

The TEA1065 can be set either in a DC voltage regulator mode or in a DC current regulator mode. The DC mask can be selected by connecting the appropriate external components to the dedicated pins (VSI, REFI, DOC, VBG).

When the DC current regulator mode is not required it can be cancelled by connecting pin VSI to V_{EE} ; pins REFI, VBG and DOC are left open-circuit.

Voltage regulator mode

The voltage regulator mode is achieved when the line current is less than the current I_{knee} as illustrated in Fig.3. With R13 = R14 = 30 k Ω , the current I_{knee} = 30 mA (I_p = 0 mA).

This line current value will be reached when the voltage on pin VSI (almost equal to the voltage on pin SLPE) exceeds the voltage on pin REFI (equal to the voltage on pin VBG divided by the resistor tap R13, R14). For other values of R13 and R14, the I_{knee} current is given by the following formula:

$$I_{knee} = I_{CC} + I_P + (VBG/R9) \times \{R14/(R14 + R13)\} - (R15/R9) \times I_O(VSI)$$

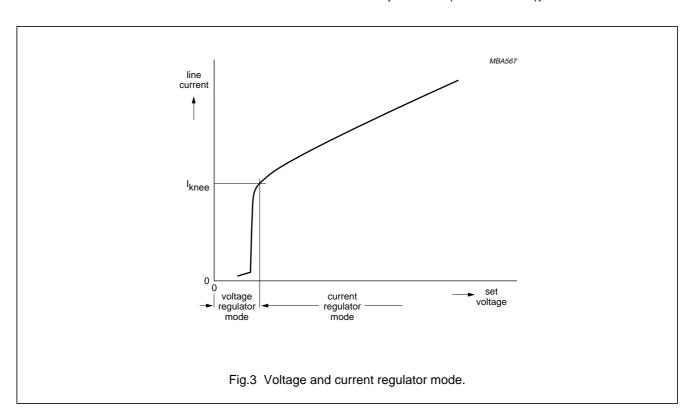
 I_{CC} is the current required by the circuit itself (typ. 1.14 mA). I_P is the current required by the peripheral circuits connected between V_{CC} and V_{EE} . $I_{O(VSI)}$ is the output current from pin VSI (typ. 2.5 μ A).

The DC slope of the V_{line}/I_{line} curve is, in this mode, determined by R9 (R9 = R9a + R9b) in series with the r_{ds} of the external line current control transistor (see Fig.4; $r_{ds} = \partial V_{GS}/\partial I_D$ at $V_{GS} = V_{DS}$).

Current regulator mode

The current regulator mode is achieved when the line current is greater than $I_{knee}.$ In this mode, the slope of the V_{line}/I_{line} curve is approximately 1300 Ω with R9 = 20 $\Omega,$ R16 = 1 M $\Omega,$ R13 = R14 = 30 k $\Omega.$ For other values of these resistances, the slope value can be approximated by the following formula:

$$R9 \times \{1 + R16 \times (1/R13 + 1/R14)\}\$$



Versatile telephone transmission circuit with dialler interface

TEA1065

The DC current flowing into the set is determined by the exchange supply voltage (V_{exch}), the DC resistance of the subscriber line (R_{line}) and the DC voltage on the subscriber set (see Fig.4).

If the line current exceeds I_{CC} + 0.3 mA, required by the circuit itself ($I_{CC} \approx 1.14$ mA), plus the current I_p required by the peripheral circuits connected to V_{CC} then the voltage regulator will divert the excess current via LN.

$$V_{LN} = V_{ref} + I_{SLPE} \times R9 = V_{ref} + (I_{line} - I_{CC} - 0.3 \times 10^{-3} - I_p) \times R9$$

where: V_{ref} is an internally generated temperature compensated reference voltage of 4.18 V and R9 is an external resistor connected between SLPE and V_{EE} .

The preferred value of R9 is 20 Ω . Changing R9 will influence the microphone gain, gain control characteristics, sidetone and the maximum output swing on LN. In this instance, the voltage on the line (excluding the diode rectifier bridge; see Fig.4) is:

$$V_{line} = V_{LN} + V_{GS} + R16 \times I_{DOC}$$

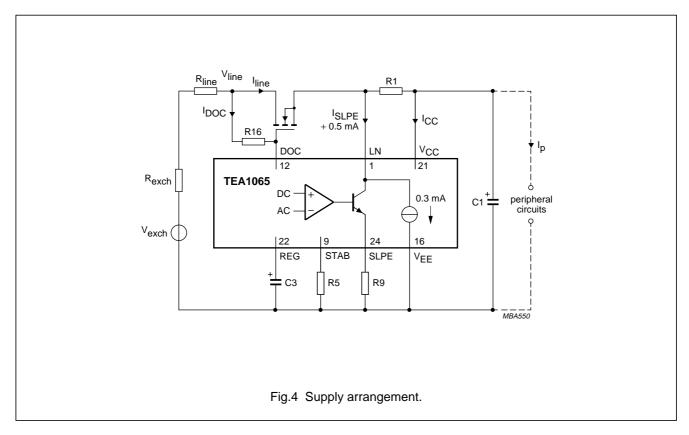
where: V_{GS} is the voltage drop between the gate and source terminal of the external line current control transistor and I_{DOC} is the current sunk by pin DOC ($I_{DOC} = 0$ in the voltage regulator mode and increases with

Iline in the current regulator mode).

Under normal conditions $I_{SLPE} >> I_{CC} + 0.3 \text{ mA} + I_p$ and for the voltage regulator mode ($I_{line} < I_{knee}$), the static behaviour of the circuit is equal to a 4.18 V voltage regulator diode with an internal resistance of R9 in series with the V_{GSon} of the external line current control transistor. For the current regulator mode ($I_{line} > I_{knee}$), the static behaviour of the circuit is equal to a 4.18 V voltage regulator diode with an internal resistance of R9 in series with the V_{GSon} of the external line current control transistor and also in series with a DC voltage source R16 \times I_{DOC} (the preferred value of R16 is 1 $M\Omega$ at this value the current I_{DOC} is negligible compared to I_{line}).

In the audio frequency range the dynamic impedance between LN and V_{EE} is equal to R1 (see Fig.8). The internal reference voltage V_{ref} can be adjusted by means of an external resistor R_{VA} . This resistor, connected between LN and REG, will decrease the internal reference voltage. When R_{VA} is connected between REG and SLPE the internal reference voltage will increase.

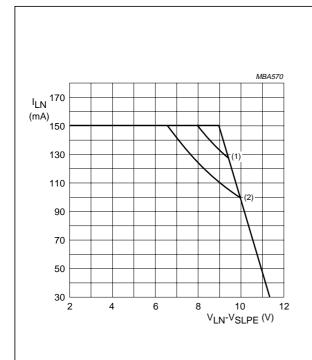
The maximum allowed line current is given in Figs 5 and 6, where the current is shown as a function of the required reference voltage, ambient temperature and applied package.



Versatile telephone transmission circuit with dialler interface

TEA1065

The current I_p, available from V_{CC} for supplying peripheral circuits, depends on the external components and on the line current. Fig.7 shows this current for V_{CC} > 2.2 V and for V_{CC} > 3 V, where 3 V is the minimum supply voltage for most CMOS circuits including a diode voltage drop for a back-up diode. If MUTE is LOW the available current is further reduced when the receiving amplifier is driven (earpiece amplifier supplied from V_{CC}).



	T _{amb}	P_{tot}
(1)	65 °C	1.2 W
(2)	75 °C	1.0 W

Fig.5 TEA1065 safe operating area.

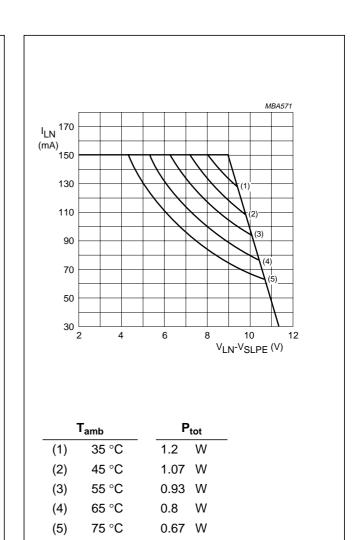
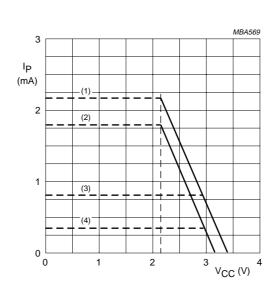


Fig.6 TEA1065T safe operating area.

Versatile telephone transmission circuit with dialler interface

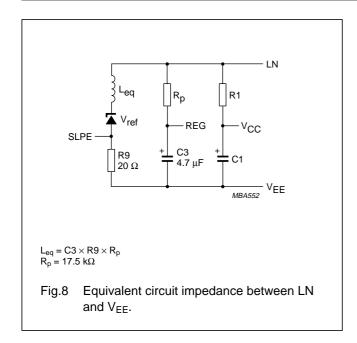
TEA1065



 I_{line} = 15 mA at V_{LN} = 4.45 V R1 = 620 Ω R9 = 20 Ω

Curve (1) and (3) are valid when the receiving amplifier is not driven or when MUTE = HIGH, curves (2) and (4) are valid when MUTE = LOW and the receiving amplifier is driven, $V_{o(rms)} = 150$ mV, $R_L = 150$ Ω (asymmetrical). (1) = 2.2 mA; (2) = 1.77 mA; (3) = 0.78 mA and (4) = 0.36 mA.

Fig.7 Maximum current I_p available from V_{CC} for external (peripheral) circuitry with $V_{CC} > 2.2$ V and $V_{CC} > 3$ V.



Versatile telephone transmission circuit with dialler interface

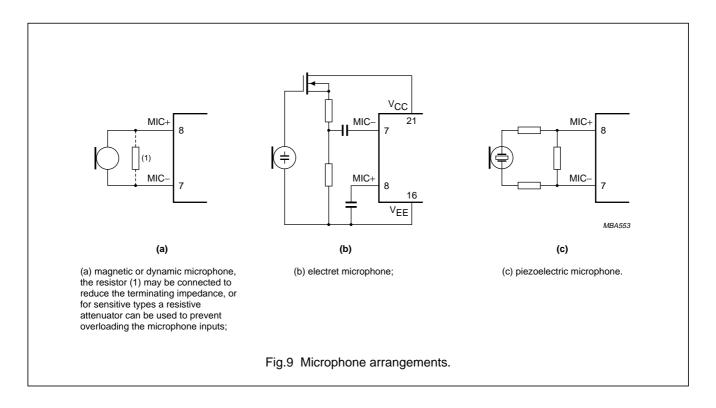
TEA1065

Microphone inputs MIC+ and MIC- and gain adjustment connections GAS1 and GAS2

The TEA1065 has symmetrical microphone inputs, its input impedance is 40.8 k Ω (2 × 20.4 k Ω) and its voltage gain is typ. 38 dB with R7 = 68 k Ω . Either dynamic, magnetic or piezoelectric microphones can be used, or an electret microphone with a built-in FET buffer. Arrangements for the microphones types are illustrated in Fig.9.

The gain of the microphone amplifier is proportional to external resistor R7, connected between GAS1 and GAS2, which can be adjusted between 30 dB and 46 dB to suit the sensitivity of the transducer.

An external 100 pF capacitor (C6) is required between GAS1 and SLPE to ensure stability. A larger value of C6 may be chosen to obtain a first-order low-pass filter. The "cut-off" frequency corresponds with the time constant $R7 \times C6$.



Versatile telephone transmission circuit with dialler interface

TEA1065

MUTE input

When MUTE = HIGH the DTMF input is enabled and the microphone and receiving amplifier inputs are inhibited. When MUTE = LOW or open-circuit the DTMF input is inhibited and the microphone and receiving amplifier inputs are enabled. Switching the MUTE input will cause negligible clicks at the earpiece outputs and on the line. An electrostatic discharge protection diode is connected between pin MUTE and pin V_{CC} (pins 20 and 21).

Dual-tone multifrequency input DTMF

When the DTMF input is enabled, dialling tones may be sent onto the line. The voltage gain from DTMF to LN is typ. 12.5 dB less than the gain of the microphone amplifier and varies with R7 in the same way as the gain of the microphone amplifier. This means that the tone level at the DTMF input has to be adjusted after setting the gain of the microphone amplifier. When R7 = 68 k Ω the gain is typically 25.5 dB. The signalling tones can be heard in the earpiece at a low level (confidence tone).

Receiving amplifiers: IR, QR+, QR- and GAR

The receiving amplifier has one input IR and two complementary outputs, QR+ (non-inverting) and

QR– (inverting). These outputs may be used for single-ended or differential drive, depending on the type and sensitivity of the earpiece used (see Fig.10). Gain from IR to QR+ is typically 31 dB with R4 = 100 k Ω , which is sufficient for low-impedance magnetic or dynamic earpieces which are suitable for single-ended drive. By using both outputs (differential drive) the gain is increased by 6 dB. Differential drive can be used when earpiece impedance exceeds 450 Ω as with high impedance dynamic, magnetic or piezoelectric earpieces.

The output voltage of the receiving amplifier is specified for continuous-wave drive. The maximum output voltage will be higher under speech conditions where the ratio of peak and RMS value is higher.

The gain of the receiving amplifier can be adjusted over a range of –11 dB to +8 dB to suit the sensitivity of the transducer that is used. The gain is proportional to external resistor R4 connected between GAR and QR+.

Two external capacitors, C4 = 100 pF and C7 = 1 nF, are necessary to ensure stability. A larger value of C4 may be chosen to obtain a first-order low-pass filter. The "cut-off" frequency corresponds with the time constant $R4 \times C4$.

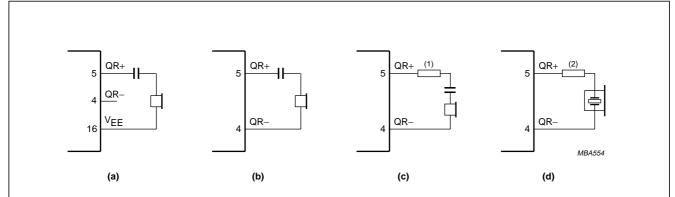


Fig.10 Alternative receiver arrangements:

- (a) dynamic earpiece with an impedance less than 450 Ω ;
- (b) dynamic earpiece with an impedance more than 450 Ω ;
- (c) magnetic earpiece with an impedance more than 450 Ω , resistor (1) may be connected to prevent distortion (inductive load);
- (d) piezoelectric earpiece, resistor (2) is required to increase the phase margin (stability with capacitive load).

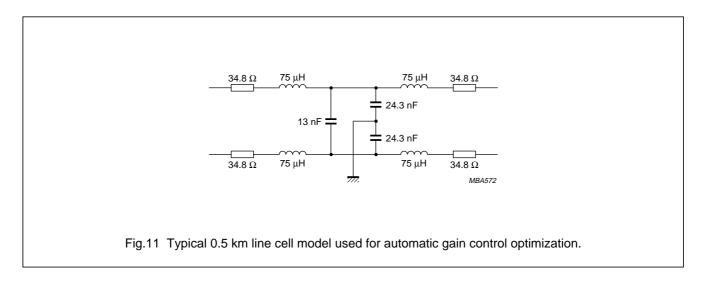
Versatile telephone transmission circuit with dialler interface

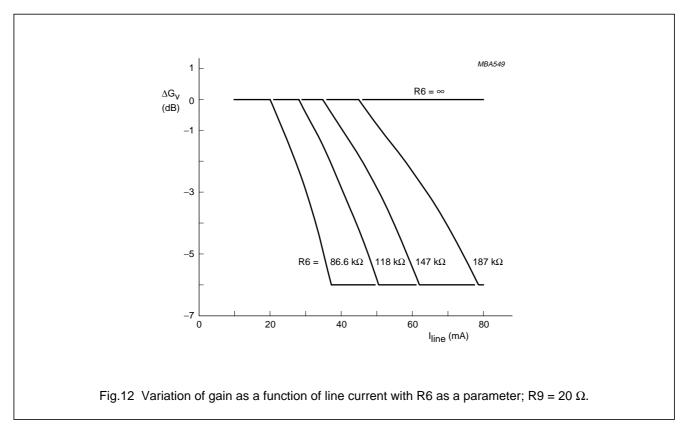
TEA1065

Automatic gain control

Automatic compensation of line loss is obtained by connecting a resistor (R6) between AGC and V_{EE} . The automatic gain control varies the gain of the microphone amplifier and receiving amplifier in accordance with the DC line current (see Fig.12). The control range is 5.9 dB; this corresponds to a line length of 3.5 km of twisted pair cable (see Fig.11). The DTMF gain is not affected by this feature.

If automatic line loss compensation is not required the AGC pin can be left open-circuit, the amplifiers then give their maximum gain.





Versatile telephone transmission circuit with dialler interface

TEA1065

Power-down input PD

During pulse dialling or register recall (timed-loop-break) the telephone line is interrupted, consequently it provides no supply for the transmission circuit and the peripherals connected to V_{CC} . These gaps have to be bridged by the charge in the smoothing capacitor C1. The requirement on this capacitor is relaxed by applying a HIGH level to the PD input during the loop-break. This reduces the internal supply current from typ. 1.14 mA to 73 μ A.

A HIGH level at PD also disconnects the capacitor at REG which results in the voltage stabilizer having no switch-on delay after line interruptions. This results in no contribution of the IC to the current waveform during pulse dialling or register recall. When this facility is not required PD may be left open-circuit or connected to $V_{\rm EE}.$ An electrostatic discharge protection diode is connected between pin PD and $V_{\rm CC}.$

Digital pulse input DPI

A HIGH level at DPI creates a current which flows from pin DOC to V_{EE} in order to interrupt the line current by the external line current control transistor (see Fig.18; MOSFET BUK554). A LOW level (or pin left open-circuit) disables this current to provide the normal DC regulation (voltage or current). A simple application without regulation of current in pulse dialling mode is given in Fig.18.

When DPI is activated (HIGH level), the external line current control transistor is switched off resulting in no current in the TEA1065. The voltage on pin SLPE becomes zero and capacitor C15 discharges cancelling the current regulation when DPI becomes inactive (LOW level).

To provide a constant regulation (in speech mode and pulse mode), an external transistor is required to keep C15 charged during DPI active (see Fig.19 in which the Field Effect Transistor BSJ177 is directly driven by the DPI signal).

An electrostatic discharge protection diode is connected between pin DPI and pin V_{CC}.

Voltage sense input and reference voltage input VSI and REFI

The voltage on pin VSI represents the DC voltage of pin SLPE. The RC filter (R15 \times C15) is also intended to disable the DC regulation when C15 is shunted or not yet charged (especially directly after hook-off). The time constant R15 \times C15 determines approximately the time when no regulation (except CURL pin limitation) is

activated.

The voltage applied on pin REFI represents a fraction of the bandgap reference voltage given by pin VBG (resistor tap R13 and R14) in order to determine I_{knee} .

Drive current output DOC

Pin DOC drives the external line current control transistor in order to achieve line interruption during pulse dialling (or register recall) and also the DC slope when $I_{\text{line}} > I_{\text{knee}}.$ The current sunk by pin DOC is determined by the voltage on pin VSI in comparison with the voltage on pin VBG divided by the resistor tap R13 and R14.

When pin DPI is activated, pin DOC changes to a low voltage (by trying to sink typ. 900 μ A to V_{EE}) to switch off the external line current control transistor.

Bandgap reference output VBG

This output provides a voltage reference to set the knee line current with the following formula:

$$I_{\text{knee}} = I_{\text{CC}} + I_{\text{P}} + (VBG/R9) \times \{R14/(R14 + R13)\} - (R15/R9) \times 2.5 \times 10^{-6}$$

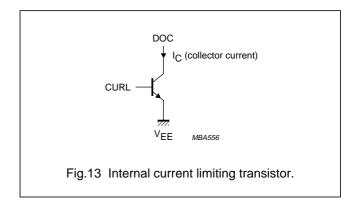
In order to improve stability, a capacitive load is not allowed on this output.

Current limit input CURL

This input is applied to the base of an internal NPN transistor which has its collector connected to pin DOC and its emitter to V_{EE} (see Fig.13). The transistor limits the line current just after hook-off or during line transients to a value given by the following formula:

$$I_{hook-off} = I(R1) + V_{BE}/R9b$$

 V_{BE} is the base-emitter voltage of the transistor (typ. 700 mV at 25 °C). I(R1) is the current flowing through R1 to charge C1 just after hook-off.



Versatile telephone transmission circuit with dialler interface

TEA1065

The maximum hook-off current then becomes:

 $I_{hook-off} = V_Z/R1 + V_{BE} \times (R9a + R9b + R1)/(R1 \times R9b)$

where V_Z is the Zener voltage of diode D5 (see Fig.18).

Side-tone suppression

Suppression of the transmitted signal in the earpiece is obtained by the anti-sidetone network comprising R1//Z $_{line}$, R2, R3, R9 and Z $_{bal}$ (see Fig.18). Maximum compensation is obtained when the following conditions are fulfilled:

a) $R9 \times R2 = R1 \times (R3 + R8)$

b) $k = R3 \times (R8 + R9)/(R2 \times R9)$

c) $Z_{bal} = k \times Z_{line}$

The scale factor k is chosen to meet the compatibility with a standard capacitor from the E6 or E12 range for Z_{bal} .

In practice Z_{line} varies considerably with the line length and line type. Therefore, the value chosen for Z_{bal} should be for an average line length giving satisfactory sidetone suppression with long and short times. The suppression

also depends on the accuracy of the match between Z_{bal} and the impedance of the average line.

Example

With k = 1, R1 = 619 Ω , R9 = 20 Ω and an average line impedance represented by 270 Ω + (120 nF // 1100 Ω), the calculation results in:

• $R2 = 130 k\Omega$

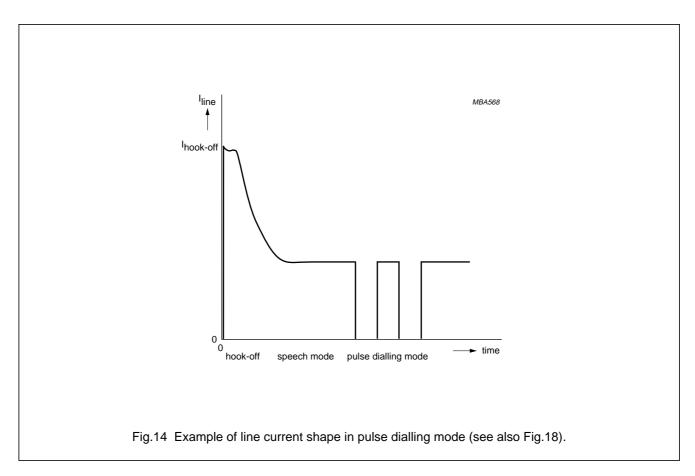
• R3 = 3650Ω

• $R8 = 715 \Omega$

The anti-sidetone network for the TEA1060 family, shown in Fig.15, attenuates the signal received from the line by 32 dB before it enters the receiving amplifier. The attenuation is almost constant over the whole audio-frequency range.

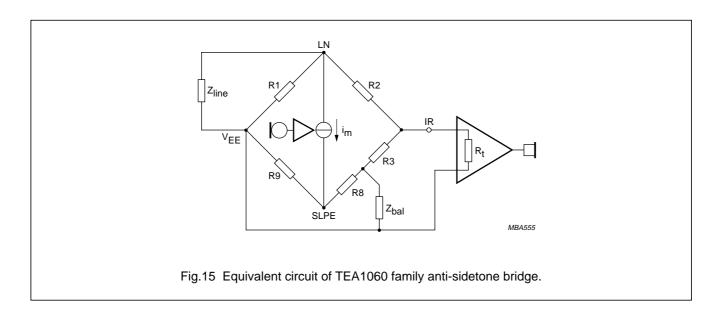
Note

More information on the balancing of the anti-sidetone bridges can be obtained in our publication "Versatile speech transmission ICs for electronic telephone sets", order number 9398 341 10011.



Versatile telephone transmission circuit with dialler interface

TEA1065



LIMITING VALUES

In accordance with the absolute maximum system (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{LN}	positive line voltage continuous		_	12	V
V _{DOC}	positive DOC voltage continuous		_	12	V
V_{LN}	repetitive line voltage during switch-on or line interruption		_	13.2	V
I _{LN}	line current (see also Fig.5 and 6)		_	150	mA
VI	input voltage on pins other than LN, DOC, VSI, REFI and CURL		V _{EE} – 0.7	V _{CC} + 0.7	V
P _{tot}	total power dissipation	see Figs 5 and 6			
T _{stg}	storage temperature range		-40	+ 125	°C
T _{amb}	operating ambient temperature range		-25	+75	°C
Tj	junction temperature		_	+125	°C

THERMAL RESISTANCE

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
R _{th j-a}	from junction to ambient in free air; TEA1065	_	50	K/W
R _{th j-a}	from junction to ambient in free air; TEA1065T (1)	_	75	K/W

Note

1. TEA1065T is mounted on glassy epoxy board $28.5 \times 19.1 \times 1.5$ mm

HANDLING

Every pin withstands the ESD test in accordance with MIL-STD-883C class 2, method 3015 (HBM 1500 Ω , 100 pF, 3 positive pulses and 3 negative pulses on each pin as a function of pin V_{EE} .

Versatile telephone transmission circuit with dialler interface

TEA1065

CHARACTERISTICS

 I_{LN} = 10 to 150 mA; V_{EE} = 0 V; f = 800 Hz; T_{amb} = 25 °C; R9 = 20 Ω ; unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Supply LN	and V _{CC} (pins 1 and 21)		•		•	•
V_{LN}	voltage drop over circuit	I _{line} = 5 mA	3.95	4.25	4.55	V
		I _{line} = 15 mA	4.25	4.45	4.65	V
		I _{line} = 100 mA	5.4	6.1	6.7	V
		I _{line} = 140 mA	_	_	7.5	V
$\Delta V_{LN}/\Delta T$	variation with temperature	I _{line} = 15 mA	-3	-1	+1	mV/K
V_{LN}	voltage drop over circuit	I _{line} = 15 mA				
		$R_{VA} = R_{1-22} = 68 \text{ k}\Omega$	3.6	3.9	4.15	V
		$R_{VA} = R_{22-24} = 39 \text{ k}\Omega$	4.7	5.0	5.3	V
I _{CC}	supply current	PD = LOW; V _{CC} = 2.8 V	_	1.14	1.5	mA
		PD = HIGH; V _{CC} = 2.8 V	_	73	105	μΑ
Micropho	ne inputs MIC+ and MIC- (pins 8 ar	nd 7)	1		•	•
Z _I	input impedance		18.5	20.4	24.3	kΩ
G_{v}	voltage gain	I_{line} = 15 mA; R7 = 68 k Ω	37	38	39	dB
$\Delta G_{v}f$	variation with frequency	$I_{line} = 15 \text{ mA};$	-0.5	±0.2	+0.5	dB
	referred to 800 Hz	f = 300 to 3400 Hz				
$\Delta G_{v}T$	variation with temperature	$I_{line} = 50 \text{ mA};$	_	±0.5	_	dB
	referred to 25 °C	$T_{amb} = -25 \text{ to } 75 ^{\circ}\text{C};$				
		without R6				
Dual-tone	multi-frequency input DTMF (pin	19)	•		•	•
z _I	input impedance		16.8	20.7	24.6	kΩ
G_{v}	voltage gain	$I_{line} = 15 \text{ mA}; R7 = 68 \text{ k}\Omega$	24.5	25.5	26.5	dB
$\Delta G_{v}f$	variation with frequency	I _{line} = 15 mA	-0.5	±0.2	+0.5	dB
	referred to 800 Hz	f = 300 to 3400 Hz				
$\Delta G_v T$	variation with temperature	$I_{line} = 50 \text{ mA};$	_	±0.5	_	dB
	referred to 25 °C	$T_{amb} = -25 \text{ to } +75 ^{\circ}\text{C}$				
Gain adju	stment GAS1 and GAS2 (pin 2 and	1	1	_	1	'
ΔG_v	gain variation with R7		-8	_	+8	dB
	connected between pins 2 and 3;					
	transmitting amplifier					

Versatile telephone transmission circuit with dialler interface

TEA1065

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Transmitti	ing amplifier output LN (pin 1)		1		!	
V _{LN(rms)}	output voltage (RMS value)	I _{line} = 15 mA				
		d _{tot} = 2%	1.9	2.3	_	V
		$d_{tot} = 10\%$	_	2.6	_	V
$V_{no(rms)}$	noise output voltage (RMS	$I_{line} = 15 \text{ mA};$	_	-68	_	dBmp
	value)	$R7 = 68 \text{ k}\Omega;$				
		pin 7 and 8 open-circuit				
		psophometrically				
		weighted (P53 curve);				
		control transistor included				
		(MOS BUK554 type see				
		Fig.18)				
Receiving	amplifier input IR (pin 17)	•		<u> </u>		
Z _I	input impedance		17	21	25	kΩ
Receiving	amplifier outputs QR+ and QR	– (pin 5 and 4)				
Z _O	output impedance		_	4	_	Ω
G_{v}	voltage gain	I_{line} = 15 mA; R4 = 100 kΩ				
		single-ended; RT = 300 Ω	30	31	32	dB
		differential; RT = 600 Ω	36	37	38	dB
$\Delta G_{v}f$	variation with frequency referred to 800 Hz			±0.2	+0.5	dB
$\Delta G_v T$	variation with temperature	without R6; I _{line} = 50 mA;	_	±0.2	_	dB
	referred to 25 °C	$T_{amb} = -25 \text{ to } +75 ^{\circ}\text{C}$				
$V_{O(rms)} \\$	output voltage (RMS value)	I _{line} = 15 mA; THD = 2%;				
		sinewave drive;				
		$R4 = 100 \text{ k}\Omega$				
		single-ended; RT = 150 Ω	0.3	0.38	_	V
		differential; RT = 450 Ω	0.56	0.72	_	V
		differential; CT = 60 nF;	0.87	1.07	_	V
		(1500 Ω series resistor);				
		f = 3400 Hz				
		I _{line} = 30 mA; differential;	1.02	1.22	_	V
		CT = 60 nF;				
		(1500 Ω series resistor);				
		f = 3400 Hz				
$V_{O(rms)}$	noise output voltage (RMS	I _{line} = 15 mA;				
. ,	value)	$R4 = 100 \text{ k}\Omega$				
		single-ended; RT = 300 Ω	_	50	_	μV
		differential; RT = 600Ω	_	100	_	μV

Versatile telephone transmission circuit with dialler interface

TEA1065

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Gain adju	stment GAR (pin 6)		•	•	•	
ΔG_v	receiving amplifier, gain		-11	_	+8	dB
	adjustment range					
Mute inpu	t MUTE (pin 20)					
V _{IH}	input voltage HIGH		1.5	_	V _{CC}	V
V_{IL}	input voltage LOW		_	_	0.3	V
I _{MUTE}	input current		_	8	15	μΑ
ΔG_v	change of microphone amplifier	MUTE = HIGH	_	-70	_	dB
	gain					
G_v	voltage gain from DTMF input	MUTE = HIGH;	-19	-17	-15	dB
	to QR+ or QR-	$R4 = 100 \text{ k}\Omega$				
		single-ended; RT = 300 Ω				
Power-do	wn input PD (pin 18)		•	•	•	
V _{IH}	input voltage HIGH		1.5	-	V _{CC}	V
V_{IL}	input voltage LOW		-	-	0.3	V
I_{PD}	input current		-	2.5	5.0	μΑ
Automatic	gain control input AGC (pin 23)	•				•
ΔG_v	controlling the gain from IR to	R6 = 118 kΩ	-5.5	-5.9	-6.3	dB
	QR+, QR- and the gain from					
	MIC+, MIC- to LN; gain control					
	range with respect to					
	I _{line} = 15 mA					
I _{line}	highest line current for		-	28	_	mA
	maximum gain					
I _{line}	lowest line current for minimum		_	50	_	mA
	gain					
ΔG_v	change of gain between		_	-1.5	_	dB
	I _{line} = 15 and 35.5 mA					
Current li	miting input CURL (pin 15)					
V _{BE}	base-emitter voltage drop of	see Fig.13;	_	0.7	_	V
	internal transistor	$I_C = 50 \mu\text{A} = I_{DOC}$				
H _{FE}	current gain of internal	see Fig.13;	60	120	_	
	transistor	$I_C = 50 \mu\text{A} = I_{DOC}$				
$I_{C(max)}$	maximum collector current of	see Fig.13	_	_	2	mA
	internal transistor					
Bandgap	reference voltage output VBG (pi	n 12)				
V_{BG}	reference voltage		_	1.22	_	V
I_{BG}	output drive capability	note 1	-100	-	+50	μΑ
Z _O	output impedance		_	12	_	Ω

Versatile telephone transmission circuit with dialler interface

TEA1065

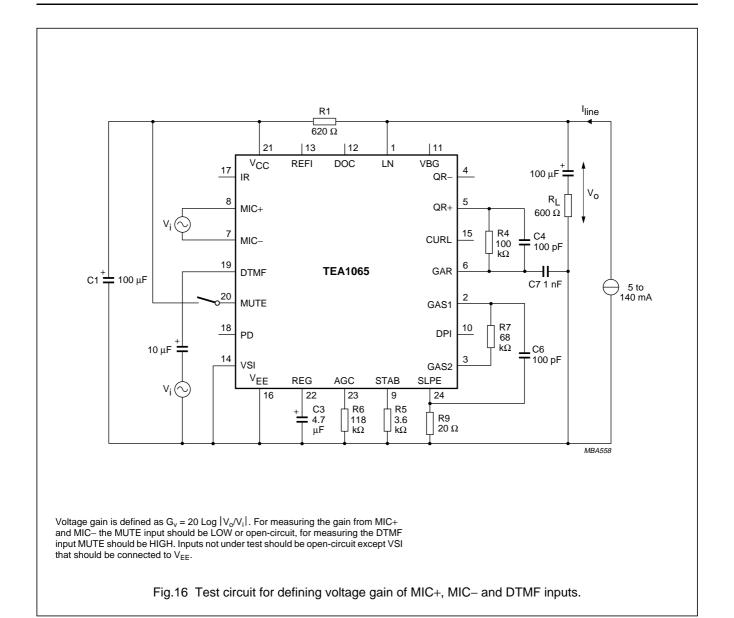
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Voltage se	ense input VSI (pin 14)		•	•		
Io	output current	pin VSI connected to V _{EE}	_	-2.5	_	μΑ
Reference	e input REFI (pin 13)		•	,	•	•
Io	output current		_	_	2.0	mA
Drive curr	ent output DOC (pin 11)					
Io	output current	REFI connected to V _{EE} ;	120	300	_	μА
		VSI not connected;				
		DPI = LOW				
		REFI not connected;	200	900	_	μΑ
		VSI connected to V _{EE} ;				
		DPI = HIGH				
Digital pu	Ise input DPI (pin 10)			•		
V _{IH}	input voltage HIGH		1.5	_	V _{CC}	V
V_{IL}	input voltage LOW		-	_	0.3	V
I _{DPI}	input current		-	2.5	5	μΑ

Note

^{1.} No capacitive load on the V_{BG} output. Positive current is defined as conventional current flow into a device. Negative current is defined as conventional current flow out of a device.

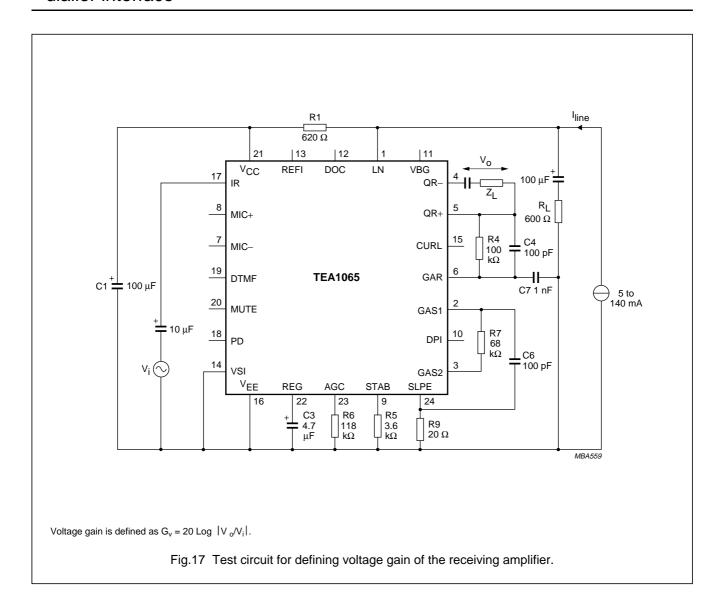
Versatile telephone transmission circuit with dialler interface

TEA1065



Versatile telephone transmission circuit with dialler interface

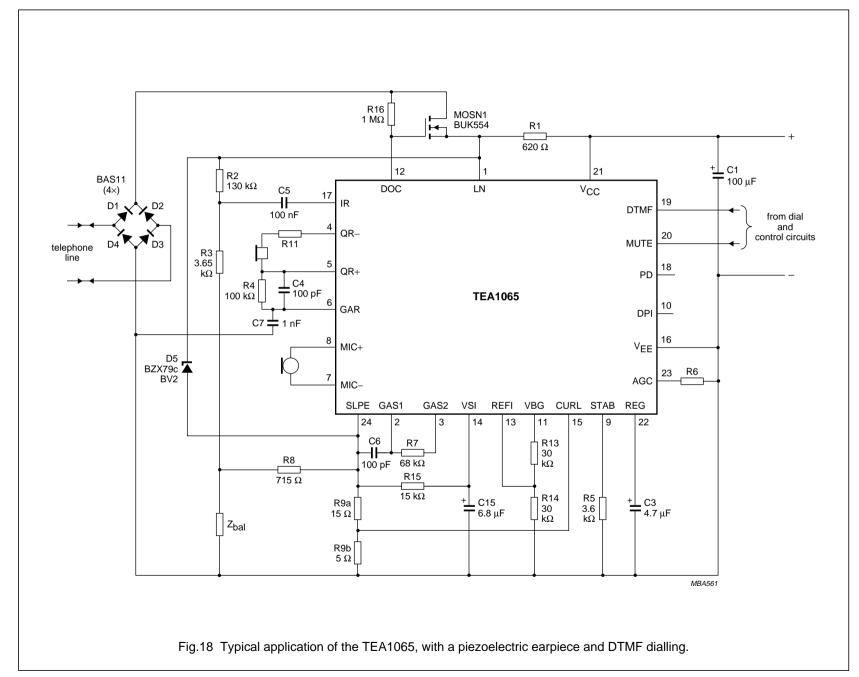
TEA1065



Product specification

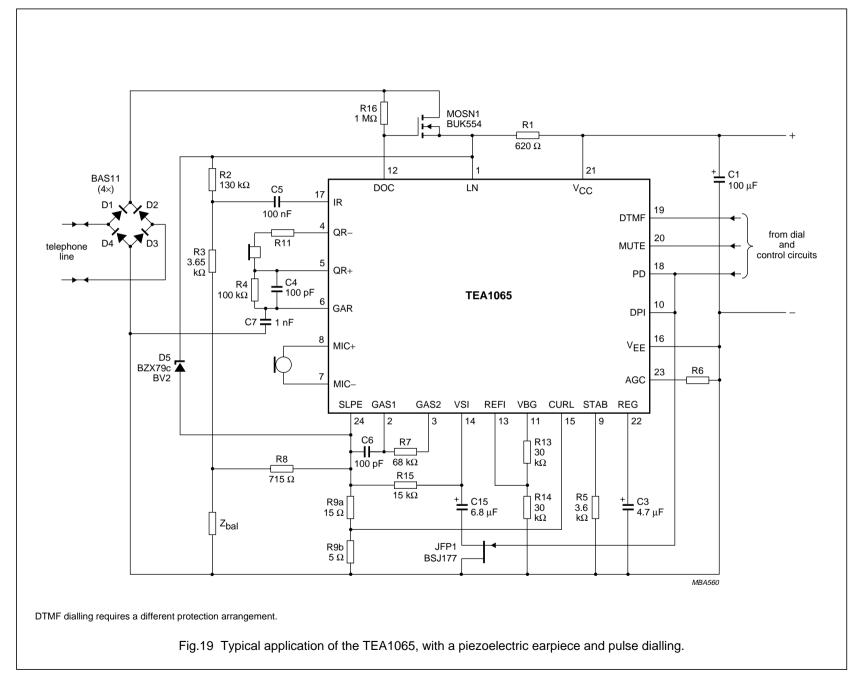
Philips Semiconductors

TEA1065



Product specification

Philips Semiconductors



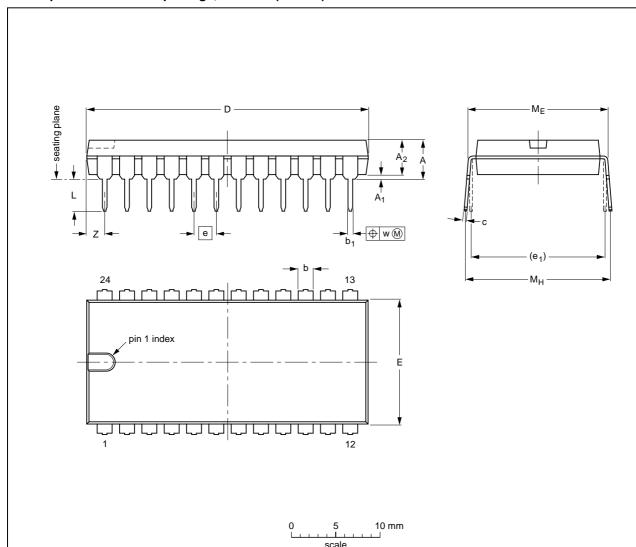
Versatile telephone transmission circuit with dialler interface

TEA1065

PACKAGE OUTLINES

DIP24: plastic dual in-line package; 24 leads (600 mil)

SOT101-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

	·														
UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	Мн	w	Z ⁽¹⁾ max.
mm	5.1	0.51	4.0	1.7 1.3	0.53 0.38	0.32 0.23	32.0 31.4	14.1 13.7	2.54	15.24	3.9 3.4	15.80 15.24	17.15 15.90	0.25	2.2
inches	0.20	0.020	0.16	0.066 0.051	0.021 0.015	0.013 0.009	1.26 1.24	0.56 0.54	0.10	0.60	0.15 0.13	0.62 0.60	0.68 0.63	0.01	0.087

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

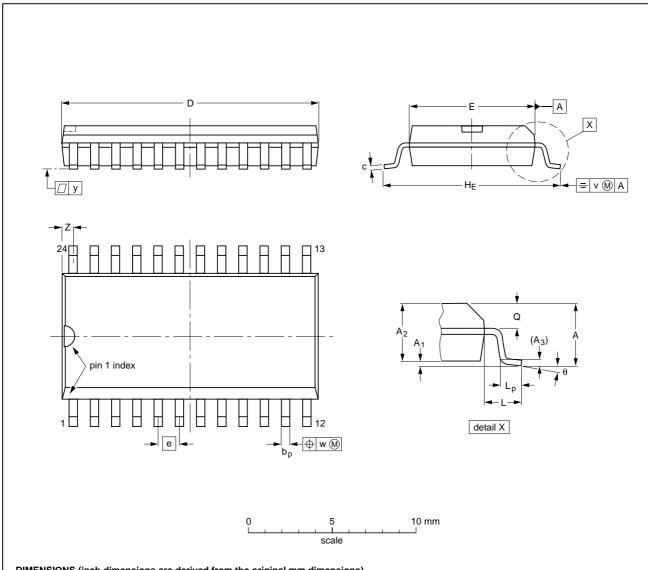
	OUTLINE		REFER	EUROPEAN	ISSUE DATE		
	VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
	SOT101-1	051G02	MO-015AD				92-11-17 95-01-23

Versatile telephone transmission circuit with dialler interface

TEA1065

SO24: plastic small outline package; 24 leads; body width 7.5 mm

SOT137-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	z ⁽¹⁾	θ
mm	2.65	0.30 0.10	2.45 2.25	0.25	0.49 0.36	0.32 0.23	15.6 15.2	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8°
inches	0.10	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.61 0.60	0.30 0.29	0.050	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	0°

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	IEC JEDEC EIAJ				ISSUE DATE	
SOT137-1	075E05	MS-013AD				95-01-24 97-05-22	

March 1994 24

Versatile telephone transmission circuit with dialler interface

TEA1065

SOLDERING

Introduction

There is no soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and surface mounted components are mixed on one printed-circuit board. However, wave soldering is not always suitable for surface mounted ICs, or for printed-circuits with high population densities. In these situations reflow soldering is often used.

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our "Data Handbook IC26; Integrated Circuit Packages" (order code 9398 652 90011).

DIP

SOLDERING BY DIPPING OR BY WAVE

The maximum permissible temperature of the solder is 260 °C; solder at this temperature must not be in contact with the joint for more than 5 seconds. The total contact time of successive solder waves must not exceed 5 seconds.

The device may be mounted up to the seating plane, but the temperature of the plastic body must not exceed the specified maximum storage temperature ($T_{stg\ max}$). If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature within the permissible limit.

REPAIRING SOLDERED JOINTS

Apply a low voltage soldering iron (less than 24 V) to the lead(s) of the package, below the seating plane or not more than 2 mm above it. If the temperature of the soldering iron bit is less than 300 °C it may remain in contact for up to 10 seconds. If the bit temperature is between 300 and 400 °C, contact may be up to 5 seconds.

SO

REFLOW SOLDERING

Reflow soldering techniques are suitable for all SO packages.

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement. Several techniques exist for reflowing; for example, thermal conduction by heated belt. Dwell times vary between 50 and 300 seconds depending on heating method. Typical reflow temperatures range from 215 to 250 °C.

Preheating is necessary to dry the paste and evaporate the binding agent. Preheating duration: 45 minutes at 45 $^{\circ}$ C.

WAVE SOLDERING

Wave soldering techniques can be used for all SO packages if the following conditions are observed:

- A double-wave (a turbulent wave with high upward pressure followed by a smooth laminar wave) soldering technique should be used.
- The longitudinal axis of the package footprint must be parallel to the solder flow.
- The package footprint must incorporate solder thieves at the downstream end.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Maximum permissible solder temperature is 260 °C, and maximum duration of package immersion in solder is 10 seconds, if cooled to less than 150 °C within 6 seconds. Typical dwell time is 4 seconds at 250 °C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

REPAIRING SOLDERED JOINTS

Fix the component by first soldering two diagonally-opposite end leads. Use only a low voltage soldering iron (less than 24 V) applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C. When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

Versatile telephone transmission circuit with dialler interface

TEA1065

DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			
Limiting values				
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or				

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

Versatile telephone transmission circuit with dialler interface

TEA1065

NOTES

Philips Semiconductors – a worldwide company

Argentina: see South America

Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113,

Tel. +61 2 9805 4455, Fax. +61 2 9805 4466

Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213, Tel. +43 160 1010,

Fax. +43 160 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,

220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773

Belgium: see The Netherlands Brazil: see South America

Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor, 51 James Bourchier Blvd., 1407 SOFIA, Tel. +359 2 689 211, Fax. +359 2 689 102

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,

Tel. +1 800 234 7381

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,

72 Tat Chee Avenue, Kowloon Tong, HONG KONG,

Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America Czech Republic: see Austria

Denmark: Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S,

Tel. +45 32 88 2636, Fax. +45 31 57 0044 Finland: Sinikalliontie 3, FIN-02630 ESPOO, Tel. +358 9 615800, Fax. +358 9 61580920

France: 51 Rue Carnot, BP317, 92156 SURESNES Cedex,

Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,

Tel. +49 40 23 53 60, Fax. +49 40 23 536 300

Greece: No. 15, 25th March Street, GR 17778 TAVROS/ATHENS,

Tel. +30 1 4894 339/239, Fax. +30 1 4814 240

Hungary: see Austria

India: Philips INDIA Ltd, Band Box Building, 2nd floor, 254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025,

Tel. +91 22 493 8541, Fax. +91 22 493 0966

Indonesia: PT Philips Development Corporation, Semiconductors Division,

Gedung Philips, Jl. Buncit Raya Kav.99-100, JAKARTA 12510, Tel. +62 21 794 0040 ext. 2501, Fax. +62 21 794 0080

Ireland: Newstead, Clonskeagh, DUBLIN 14 Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053, TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3, 20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108-8507, Tel. +81 3 3740 5130, Fax. +81 3 3740 5077

Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,

Tel. +82 2 709 1412, Fax. +82 2 709 1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,

Tel. +60 3 750 5214, Fax. +60 3 757 4880

Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,

Tel. +9-5 800 234 7381

Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,

Tel. +31 40 27 82785, Fax. +31 40 27 88399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,

Tel. +64 9 849 4160. Fax. +64 9 849 7811 Norway: Box 1, Manglerud 0612, OSLO, Tel. +47 22 74 8000, Fax. +47 22 74 8341

Pakistan: see Singapore

Philippines: Philips Semiconductors Philippines Inc., 106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI, Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: UI. Lukiska 10, PL 04-123 WARSZAWA, Tel. +48 22 612 2831, Fax. +48 22 612 2327

Portugal: see Spain Romania: see Italy

Russia: Philips Russia, UI. Usatcheva 35A, 119048 MOSCOW,

Tel. +7 095 755 6918, Fax. +7 095 755 6919

Singapore: Lorong 1, Toa Payoh, SINGAPORE 319762,

Tel. +65 350 2538, Fax. +65 251 6500

Slovakia: see Austria Slovenia: see Italy

South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,

2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000,

Tel. +27 11 470 5911, Fax. +27 11 470 5494

South America: Al. Vicente Pinzon, 173, 6th floor, 04547-130 SÃO PAULO, SP, Brazil, Tel. +55 11 821 2333, Fax. +55 11 821 2382

Spain: Balmes 22, 08007 BARCELONA Tel. +34 93 301 6312, Fax. +34 93 301 4107

Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM,

Tel. +46 8 5985 2000, Fax. +46 8 5985 2745

Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH, Tel. +41 1 488 2741 Fax. +41 1 488 3263

Taiwan: Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1,

TAIPEI, Taiwan Tel. +886 2 2134 2865, Fax. +886 2 2134 2874

Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd.

209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260,

Tel. +66 2 745 4090, Fax. +66 2 398 0793

Turkey: Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL,

Tel. +90 212 279 2770. Fax. +90 212 282 6707

Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,

252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461 United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes,

MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421

United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,

Tel. +1 800 234 7381

Uruguay: see South America Vietnam: see Singapore

Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,

Tel. +381 11 625 344, Fax.+381 11 635 777

For all other countries apply to: Philips Semiconductors, International Marketing & Sales Communications, Building BE-p, P.O. Box 218, 5600 MD EINDHOVEN, The Netherlands, Fax. +31 40 27 24825

© Philips Electronics N.V. 1998

SCA60

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

415102/00/02d/pp28

Date of release: March 1994

Document order number: 9397 750 nnnnn

Let's make things better.

Internet: http://www.semiconductors.philips.com



